

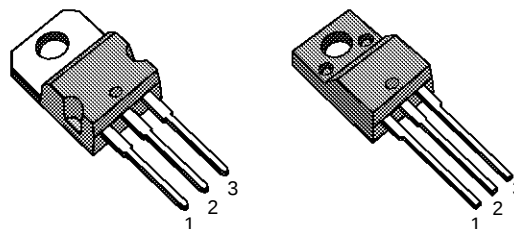
HIGH VOLTAGE IGNITION COIL DRIVER NPN POWER DARLINGTON

PRELIMINARY DATA

- VERY RUGGED BIPOLAR TECHNOLOGY
- BUILT IN CLAMPING ZENER
- HIGH OPERATING JUNCTION TEMPERATURE
- WIDE RANGE OF PACKAGES
- POWER PACKAGE SPECIFICALLY DESIGNED FOR SURFACE MOUNTING (Power SO-10™)

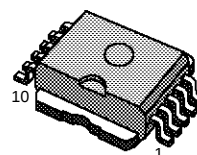
APPLICATIONS

- HIGH RUGGEDNESS ELECTRONIC IGNITIONS



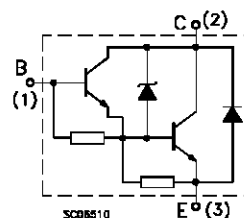
TO-220

ISOWATT220



Power SO-10™

INTERNAL SCHEMATIC DIAGRAM



for **Power SO-10**
 Emitter: pins 1 - 5
 Base: pins 6 - 10
 Collector: tab

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value			Unit
		BU941ZT	BU941ZTFI	BU941ZSM	
V _{CEO}	Collector-Emitter Voltage (I _B = 0)	350			V
V _{EBO}	Emitter-Base Voltage (I _C = 0)	5			V
I _C	Collector Current	15			A
I _{CM}	Collector Peak Current	30			A
I _B	Base Current	1			A
I _{BM}	Base Peak Current	5			A
P _{tot}	Total Dissipation at T _c = 25 °C	150	55	150	W
T _{stg}	Storage Temperature	-65 to 175	-65 to 150	-65 to 175	°C
T _j	Max. Operating Junction Temperature	175	150	175	°C

THERMAL DATA

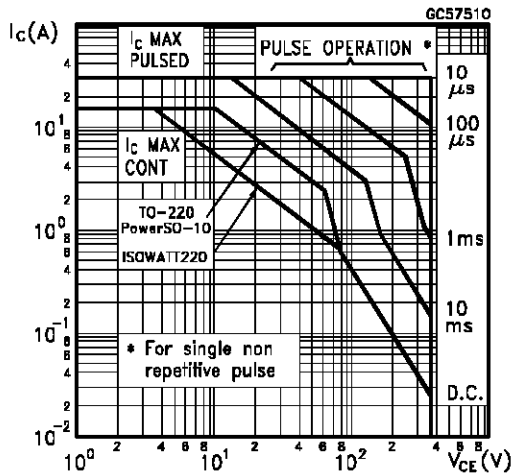
		TO-220	ISOWATT220	PowerSO-10	
$R_{thj-case}$	Thermal Resistance Junction-case Max	1	2.7	1	°C/W

ELECTRICAL CHARACTERISTICS ($T_{case} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

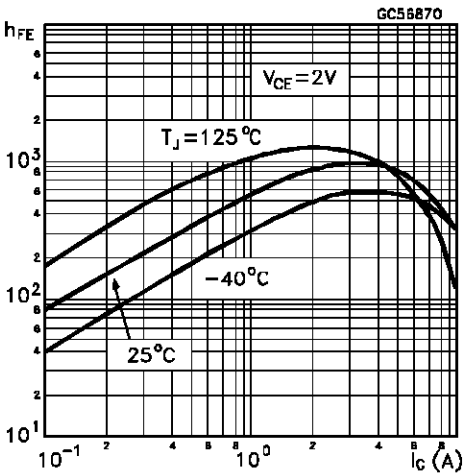
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CEO}	Collector Cut-off Current ($I_B = 0$)	$V_{CE} = 300\text{ V}$ $V_{CE} = 300\text{ V}$ $T_j = 125\text{ }^{\circ}\text{C}$			100 0.5	μA mA
I_{EBO}	Emitter Cut-off Current ($I_C = 0$)	$V_{EB} = 5\text{ V}$			20	mA
V_{CL}^*	Clamping Voltage	$I_C = 100\text{ mA}$	350		500	V
$V_{CE(sat)}^*$	Collector-Emitter Saturation Voltage	$I_C = 8\text{ A}$ $I_B = 100\text{ mA}$ $I_C = 10\text{ A}$ $I_B = 250\text{ mA}$			1.8 1.8	V V
$V_{BE(sat)}^*$	Base-Emitter Saturation Voltage	$I_C = 8\text{ A}$ $I_B = 100\text{ mA}$ $I_C = 10\text{ A}$ $I_B = 250\text{ mA}$			2.2 2.5	V V
h_{FE}^*	DC Current Gain	$I_C = 5\text{ A}$ $V_{CE} = 10\text{ V}$	300			
V_F	Diode Forward Voltage	$I_F = 10\text{ A}$			2.5	V
	Functional Test (see fig. 1)	$V_{CC} = 24\text{ V}$ $L = 7\text{ mH}$	10			A
t_s t_f	INDUCTIVE LOAD Storage Time Fall Time (see fig. 3)	$V_{CC} = 12\text{ V}$ $L = 7\text{ mH}$ $V_{clamp} = 300\text{ V}$ $I_C = 7\text{ A}$ $I_B = 70\text{ mA}$ $V_{BE} = 0$ $R_{BE} = 47\text{ }\Omega$		15 0.5		μs μs

* Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

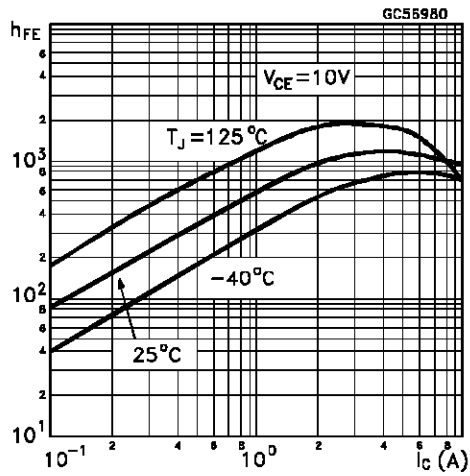
Safe Operating Areas



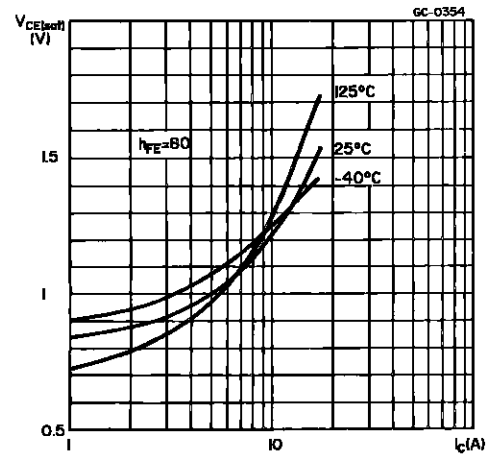
DC Current Gain



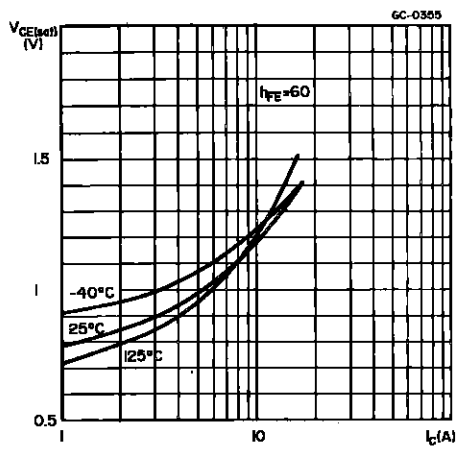
DC Current Gain



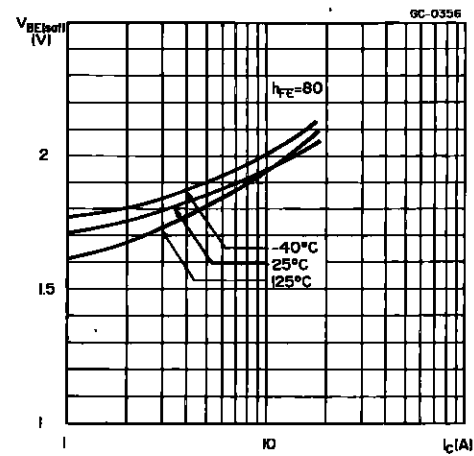
Collector-emitter Saturation Voltage



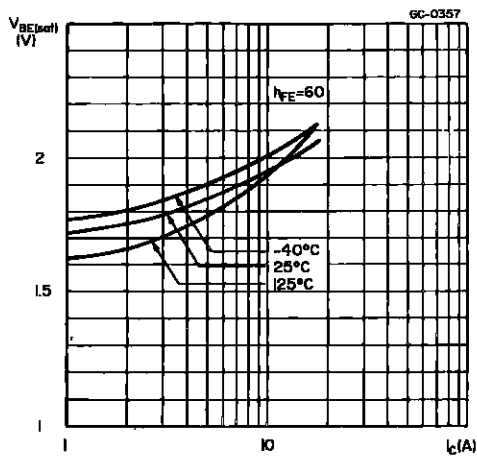
Collector-emitter Saturation Voltage



Base-emitter Saturation Voltage



Base-emitter Saturation Voltage



Collector-emitter Saturation Voltage

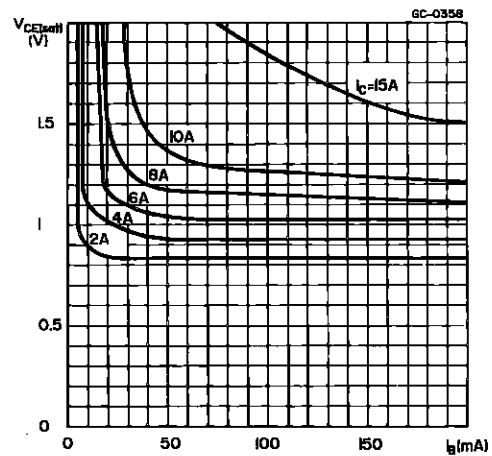


FIGURE 1: Functional Test Circuit

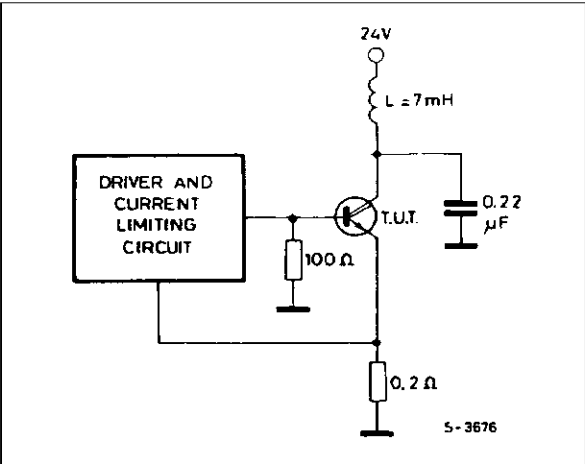


FIGURE 2: Functional Test Waveform

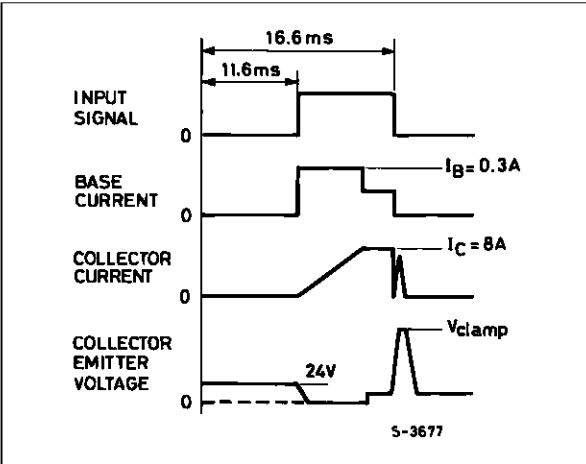
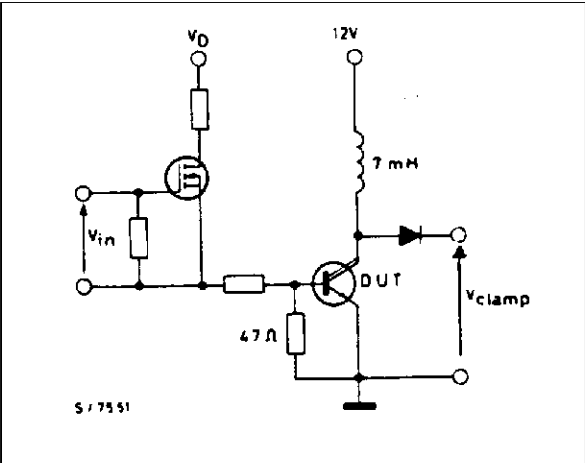
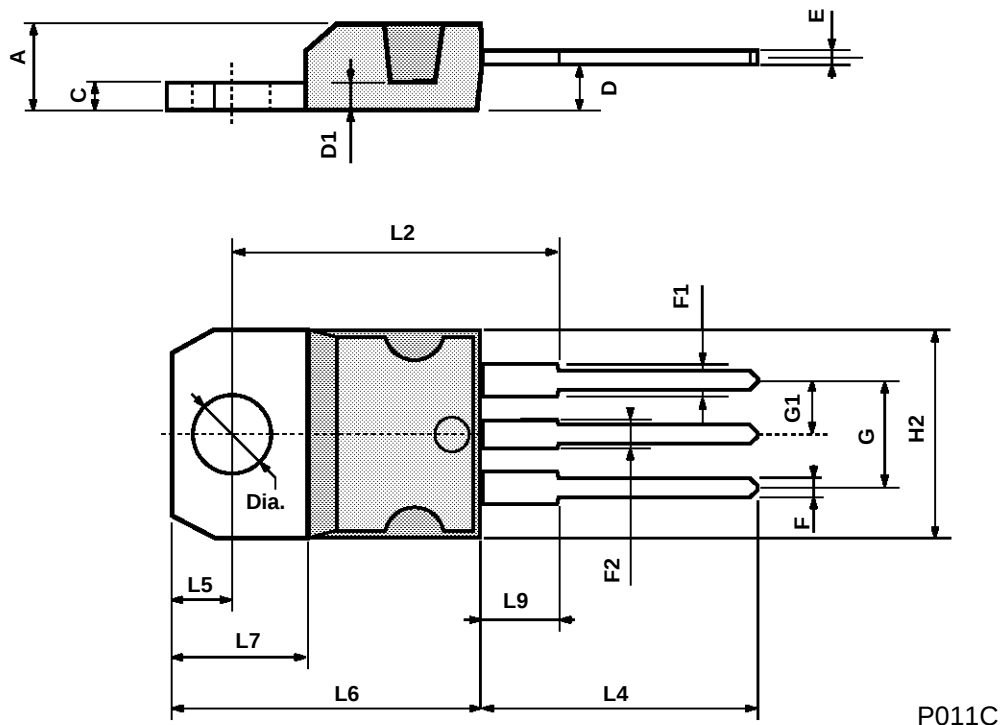


FIGURE 3: Switching Time Test Circuit



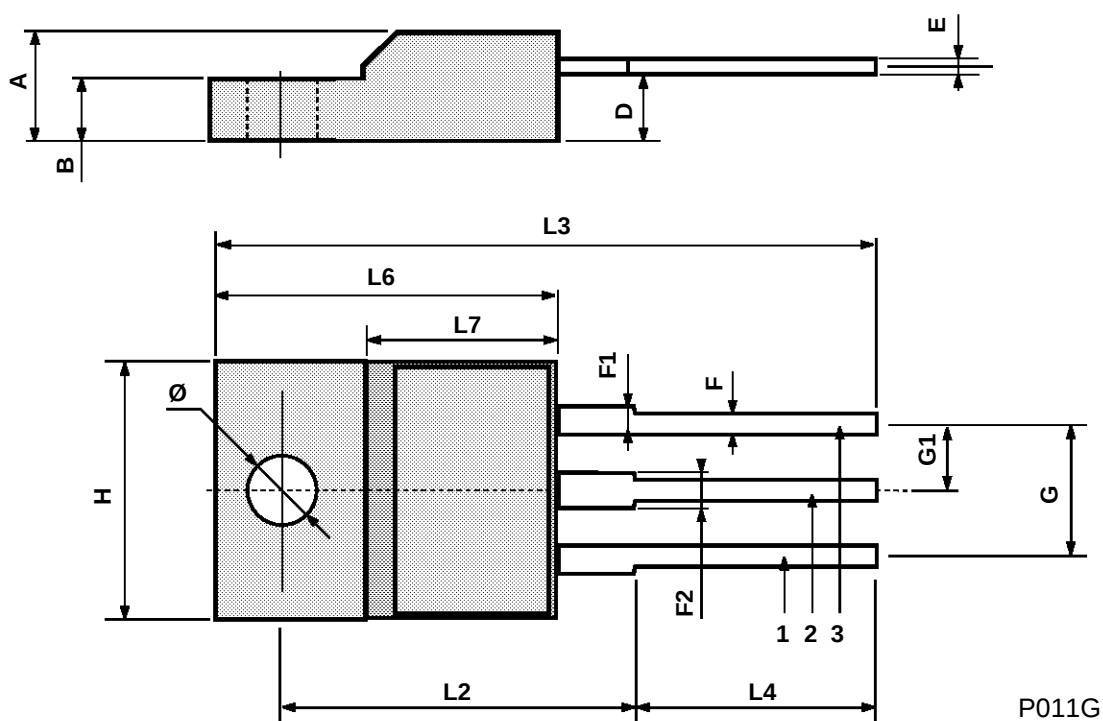
TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



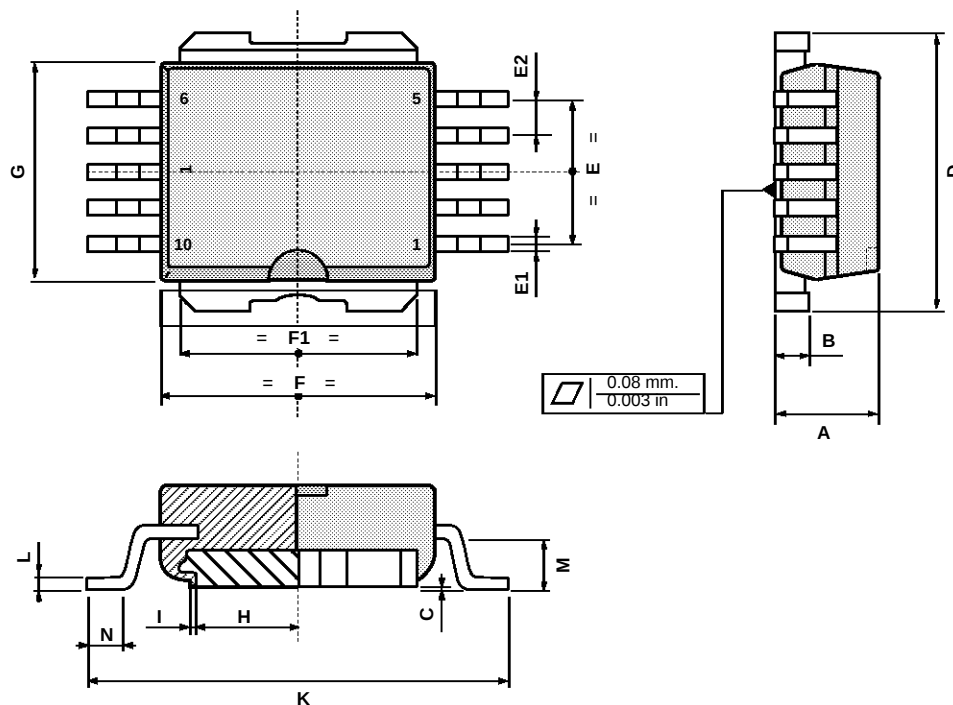
ISOWATT220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.4		0.7	0.015		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	0.385		0.417
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



Power SO-10 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	3.45	3.5	3.55	0.135	0.137	0.140
B		1.28	1.30		0.050	0.051
C			0.15			0.006
D	9.40	9.50	9.60	0.370	0.374	0.378
E	4.98	5.08	5.48	0.196	0.200	0.216
E1	0.40	0.45	0.60	0.016	0.018	0.024
E2	1.17	1.27	1.37	0.046	0.050	0.054
F	9.30	9.40	9.50	0.366	0.370	0.374
F1	7.95	8.00	8.15	0.313	0.315	0.321
G	7.40	7.50	7.60	0.291	0.295	0.299
H	6.80	6.90	7.00	0.267	0.417	0.421
I		0.10			0.004	
K	13.80	14.10	14.40	0.543	0.555	0.567
L		0.40	0.50		0.016	0.020
M	1.60	1.67	1.80	0.063	0.066	0.071
N	0.60	0.08	1.00	0.024	0.031	0.039



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